High Current Transistors

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-80	Vdc
Collector – Base Voltage	V _{CBO}	-80	Vdc
Emitter – Base Voltage	V _{EBO}	-4.0	Vdc
Collector Current – Continuous	Ic	-1.0	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

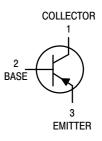
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	83.3	°C/W



ON Semiconductor®

http://onsemi.com





DIAGRAM



MARKING

BC490A = Device Code A = Assembly Location

TO-92

CASE 29

STYLE 17

Y = Year
WW = Work Week
= Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

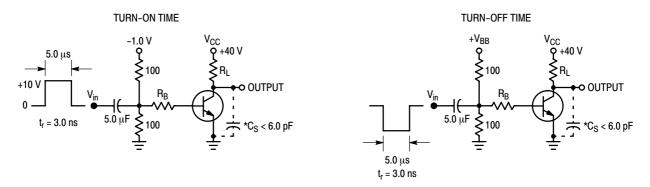
Device	Package	Shipping
BC490	TO-92	5000 Units / Box
BC490G	TO-92 (Pb-Free)	5000 Units / Box
BC490A	TO-92	5000 Units / Box
BC490AG	TO-92 (Pb-Free)	5000 Units / Box
BC490AZL1	TO-92	2000 / Ammo Box
BC490AZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

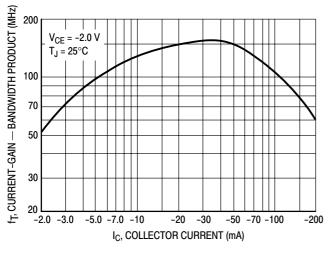
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 1) (I _C = -10 mAdc, I _B = 0)	V _{(BR)CEO}	-80	_	-	Vdc
Collector – Base Breakdown Voltage (I _C = –100 μAdc, I _E = 0)	V _{(BR)CBO}	-80	_	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \mu Adc$, $I_C = 0$)	V _{(BR)EBO}	-4.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = -60 \text{ Vdc}, I_E = 0)$	I _{CBO}	-	_	-100	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_{C} = -10 \text{ mAdc, } V_{CE} = -2.0 \text{ Vdc)} \\ &(I_{C} = -100 \text{ mAdc, } V_{CE} = -2.0 \text{ Vdc)} \end{aligned} \qquad &\text{BC490} \\ &(I_{C} = -1.0 \text{ Adc, } V_{CE} = -5.0 \text{ Vdc)} \end{aligned} $	h _{FE}	40 60 100 15	- - 140 -	- 400 250 -	-
Collector – Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$) ($I_C = -1.0 \text{ Adc}$, $I_B = -100 \text{ mAdc}$)	V _{CE(sat)}	_ _	-0.25 -0.5	-0.5 -	Vdc
Base – Emitter Saturation Voltage ($I_C = -500$ mAdc, $I_B = -50$ mAdc) ($I_C = -1.0$ Adc, $I_B = -100$ mAdc)	V _{BE(sat)}	_ _	-0.9 -1.0	-1.2 -	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain – Bandwidth Product (I _C = -50 mAdc, V _{CE} = -2.0 Vdc, f = 100 MHz)	f _T	_	150	_	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	-	9.0	-	pF
Input Capacitance $(V_{EB} = -0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	C _{ib}	-	110	-	pF

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle 2%.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits



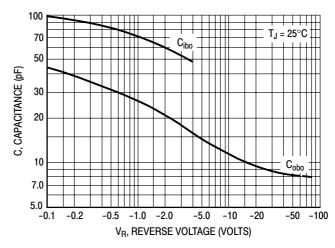


Figure 2. Current-Gain — Bandwidth Product

Figure 3. Capacitance

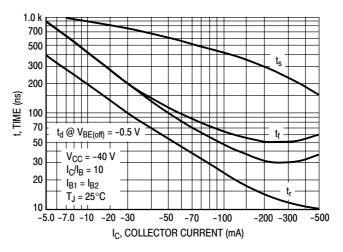


Figure 4. Switching Time

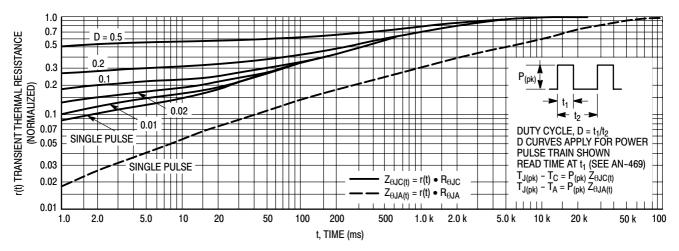


Figure 5. Thermal Response

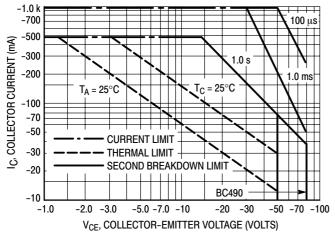


Figure 6. Active Region, Safe Operating Area

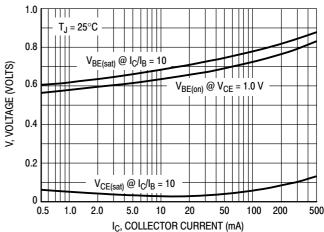


Figure 7. "On" Voltages

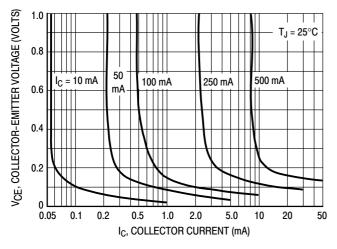


Figure 8. Collector Saturation Region

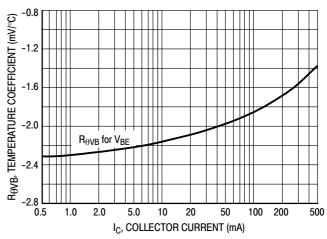


Figure 9. Base-Emitter Temperature Coefficient

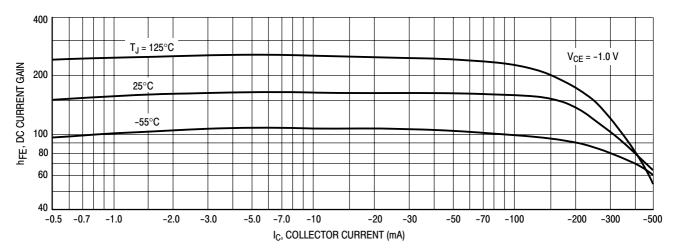
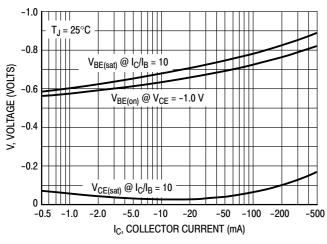


Figure 10. DC Current Gain



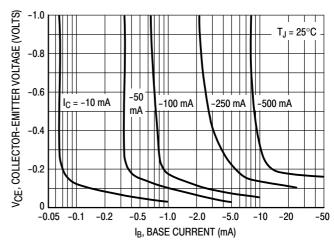


Figure 11. "On" Voltages

Figure 12. Collector Saturation Region

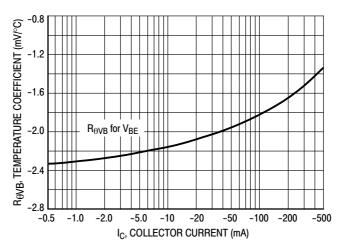
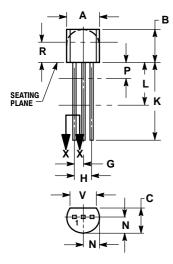


Figure 13. Base-Emitter Temperature Coefficient

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- 7/14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 17:

PIN 1. COLLECTOR

- BASE
- 3. EMITTER

ON Semiconductor and una are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered readerlands of semiconductor Components industries, Ltc (SCILLC). Solitude services the inject that changes without further holice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications. intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.